ABSTRACT

METHOD OF HARD MASK PATTERNING

A method of patterning a hard mask, the comprising the following steps. A semiconductor structure is provided. A conductor film is formed over the semiconductor structure. An oxide layer is formed over the conductor film. A patterned metal oxide layer is formed over the conductor film. The oxide layer and the conductor film are etched, using the metal oxide layer as a hard mask, to form a patterned structure.

(FIGURE 1 IS SUGGESTED FOR PUBLICATION)